Title (en)

MONOLITHIC SILICON WAFER HAVING ALTERNATING N-DOPED AREAS AND P-DOPED AREAS

Title (de)

MONOLITHISCHER SILICIUMWAFER MIT ALTERNIERENDEN N-DOTIERTEN UND P-DOTIERTEN BEREICHEN

Title (fr)

PLAQUETTE DE SILICIUM MONOLITHIQUE PRESENTANT UNE ALTERNANCE DE ZONES DOPEES N ET DE ZONES DOPEES P

Publication

EP 2965362 A1 20160113 (FR)

Application

EP 14713263 A 20140306

Priority

- FR 1352096 A 20130308
- IB 2014059497 W 20140306

Abstract (en)

[origin: WO2014136082A1] The present invention concerns a monolithic silicon wafer (10) having, in at least a vertical cutting plane, alternating n-doped areas (110) and p-doped areas (120), each of the areas extending over the entire thickness (e) of the wafer, characterised in that: - said n-doped areas (110) and p-doped areas (120) each have, in the cutting plane, a width (L1, L2) of at least 1 mm; - the n-doped areas (110) have a concentration of oxygen thermal donors different from that of the p-doped areas (120); and - said n-doped areas (110) and said p-doped areas are separated from each other by electrical insulation areas (130). It also concerns methods of producing such a wafer.

IPC 8 full level

H01L 31/0352 (2006.01); **H01L 21/761** (2006.01); **H01L 27/142** (2006.01); **H01L 31/068** (2012.01); **H01L 31/0687** (2012.01); **H01L 31/18** (2006.01)

CPC (source: EP)

H01L 21/761 (2013.01); **H01L 31/03529** (2013.01); **H01L 31/047** (2014.12); **H01L 31/068** (2013.01); **H01L 31/1804** (2013.01); H01L 31/0687 (2013.01); Y02E 10/547 (2013.01); Y02P 70/50 (2015.11)

Citation (search report)

See references of WO 2014136082A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

WO 2014136082 A1 20140912; CN 105190863 A 20151223; EP 2965362 A1 20160113; FR 3003089 A1 20140912; FR 3003089 B1 20150410

DOCDB simple family (application)

IB 2014059497 W 20140306; CN 201480024908 A 20140306; EP 14713263 A 20140306; FR 1352096 A 20130308